## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

## B. <u>Amendments to the Specification</u>.

Please replace the title beginning on Page 1, Line 1 with the following:

## 5 SEMICONDUCTOR DEVICE INCLUDING AN INSULATED GATE FIELD EFFECT TRANSISTOR AND METHOD OF MANUFACTING THE SAME

Please insert the following at Page 1, Line 5 (after the title but before the "TECHNICAL FIELD"):

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This application is a divisional of patent application Serial No. 09/991,093 filed November 13, 2001.

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